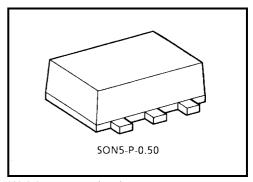
TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7SZ126AFE

### **Dual Bus Buffer 3-State Output**

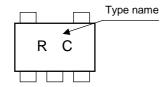
#### **Features**

- High output drive: ±24 mA (min) @VCC = 3 V
- Super high speed operation:  $t_{pd}$  2.6 ns (typ.) @VCC = 5 V, 50 pF
- Operation voltage range:  $V_{CC \text{ (opr)}} = 1.8 \sim 5.5 \text{ V}$
- Latch-up performance: ±500 mA or more
- ESD performance: ±200 V or more (JEITA) ±2000 V or more (MIL)
- Power down protection is provided on all inputs and outputs.
- $\bullet$  Matches the performance of TC74LCX series when operated at 3.3 V VCC.

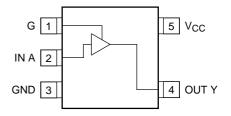


Weight: 0.003 g (typ.)

### Marking



# Pin Assignment (top view)



# **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	-0.5~6	V
DC input voltage	V <sub>IN</sub>	-0.5~6	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±50	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	150	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C
Lead temperature (10s)	TL	260	°C

# **Truth Table**

А	G	Υ
Х	L	Z
L	Н	L
Н	Н	Н

# Logic Diagram



# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	Vcc	1.8~5.5	V
Supply voltage	vCC	1.5~5.5 (Note)	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
		$0 \sim 20 \; (V_{CC} = 1.8 \; V, \; 2.5 \; V \pm 0.2 \; V)$	ns/V
Input rise and fall time	dt/dv	0~10 (V <sub>CC</sub> = 3.3 V $\pm$ 0.3 V)	
		$0~5~(V_{CC} = 5.5~V \pm 0.5~V)$	

Note: Data retention only

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# **Electrical Characteristics**

# **DC Characteristics**

Characteristics S		Symbol	Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
		Symbol			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
		.,	_		1.8	0.75 × V <sub>CC</sub>		_	0.75 × V <sub>CC</sub>	_	. V
High level	V <sub>IH</sub>	2.3~5.5			0.7 × V <sub>CC</sub>	_	_	0.7 × V <sub>CC</sub>	_		
Input voltage				1.8	—		0.25 × V <sub>CC</sub>	_	0.25 × V <sub>CC</sub>		
	Low level	V <sub>IL</sub>	_		2.3~5.5	_	_	0.3 × V <sub>CC</sub>	_	0.3 × V <sub>CC</sub>	
					1.8	1.7	1.8	_	1.7	_	
				I <sub>OH</sub> = -100 μA	2.3	2.2	2.3	_	2.2	_	
				ΙΟΗ = – 100 μΑ	3.0	2.9	3.0	_	2.9	_	
	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		4.5	4.4	4.5	_	4.4	_	
	riigirievei			$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.15	_	1.9	_	
				$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.8	_	2.4	_	
Outside and leave				I <sub>OH</sub> = -24 mA	3.0	2.3	2.68	_	2.3	_	
			$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.2	_	3.8	_	V	
Output voltage		V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub>	$I_{OL} = 100 \ \mu A$	1.8	_	0	0.1	_	0.1	
					2.3	_	0	0.1	_	0.1	
					3.0	_	0	0.1		0.1	
	Lowlovol				4.5	_	0	0.1	_	0.1	
Low level	LOW level			$I_{OL} = 8 \text{ mA}$	2.3	_	0.1	0.3	_	0.3	
				$I_{OL} = 16 \text{ mA}$	3.0	_	0.15	0.4	_	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	_	0.22	0.55	_	0.55	
				I <sub>OL</sub> = 32 mA	4.5	_	0.22	0.55	_	0.55	
Input leakage current $I_{IN}$ $V_{IN} = 5.5 \text{ V or GND}$		0~5.5	—		±1	_	±10	μΑ			
3-state output off-st	B-state output off-state current $I_{OZ}$ $V_{IN} = V_{IH}$ or $V_{IL}$ , $V_{OUT} = 0 \sim 5.5 \text{ V}$		1.8~5.5	_		±1	_	±10	μА		
Power off leakage of	wer off leakage current I <sub>OFF</sub> V <sub>IN</sub> or V <sub>OUT</sub> = 5.5 V		0.0			1	_	10	μΑ		
Quiescent supply current $I_{CC}$ $V_{IN} = 5.5 \text{ V or GND}$		5.5	_		2	_	20	μΑ			

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# AC Characteristics (unless otherwise specified, Input: $t_r = t_f = 3$ ns)

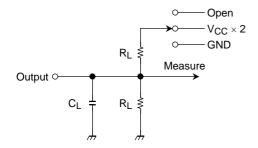
Characteristics	Cumhal	Symbol Test Condition		Ta = 25°C		Ta = -40~85°C		Unit	
Gridiaciensiics Symbo		rest Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
		$C_L$ = 15 pF, $R_L$ = 1 $M\Omega$	1.8	2.0	5.3	11.0	2.0	11.5	
			$2.5\pm0.2$	0.8	3.4	7.5	0.8	8.0	
Propagation delay time	t <sub>pLH</sub>		$3.3 \pm 0.3$	0.5	2.5	5.2	0.5	5.5	
Fropagation delay time	t <sub>pHL</sub>		$5.0 \pm 0.5$	0.5	2.1	4.5	0.5	4.8	
		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	$3.3 \pm 0.3$	1.5	3.2	5.7	1.5	6.0	
			$5.0 \pm 0.5$	0.8	2.6	5.0	0.8	5.3	
Output enable time			1.8	2.0	6.5	11.5	2.0	12.0	ns
	t <sub>pZH</sub>	$C_1 = 50 \text{ pF}, R_1 = 500 \Omega$	$2.5\pm0.2$	1.5	3.8	8.0	1.5	8.5	- 115
			$3.3 \pm 0.3$	1.5	3.2	5.7	1.5	6.0	
			$5.0 \pm 0.5$	0.8	2.3	5.0	0.8	5.3	
Output disable time			1.8	2.0	5.6	11.0	2.0	12.0	
	t <sub>pLZ</sub>	C. 50 pE B. 500 O	$2.5\pm0.2$	1.0	4.0	8.0	1.5	8.5	
	t <sub>pHZ</sub>	$C_{L} = 50 \text{ pr}, R_{L} = 500 \Omega$	$3.3 \pm 0.3$	1.0	3.5	5.7	1.0	6.0	
			$5.0 \pm 0.5$	0.5	2.7	4.7	0.5	5.0	
Input capacitance	C <sub>IN</sub>		0~5.5	_	4	_	_	_	pF
Power dissipation	C <sub>PD</sub>	(Note)	3.3	_	20	_	_	_	ьE
capacitance	OPD	C <sub>PD</sub> (Note)			27			_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

### **AC Characteristics Measurement Circuit**

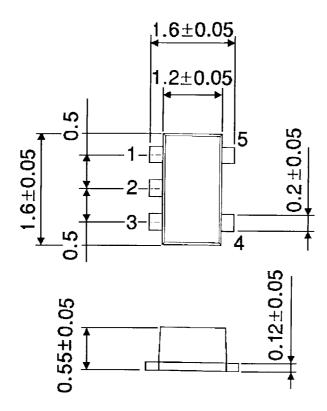


Characteristics	Switch
t <sub>pLH</sub> , t <sub>pHL</sub>	Open
t <sub>pLZ</sub> , t <sub>pZL</sub>	$V_{CC}\times 2$
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND

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# **Package Dimensions**

SON5-P-0.50 Unit: mm



Weight: 0.003 g (typ.)

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